600 Watt Peak Power Zener Transient Voltage Suppressors

Unidirectional*

The SMB series is designed to protect voltage sensitive components from high voltage, high energy transients. They have excellent clamping capability, high surge capability, low zener impedance and fast response time. The SMB series is supplied in ON Semiconductor's exclusive, cost-effective, highly reliable SURMETIC[®] package and is ideally suited for use in communication systems, automotive, numerical controls, process controls, medical equipment, business machines, power supplies and many other industrial/consumer applications.

Specification Features:

- Working Peak Reverse Voltage Range 5.8 to 171 V
- Standard Zener Breakdown Voltage Range 6.8 to 200 V
- Peak Power 600 W @ 1 ms
- ESD Rating of Class 3 (> 16 kV) per Human Body Model
- Maximum Clamp Voltage @ Peak Pulse Current
- Low Leakage < 5 μA Above 10 V
- UL 497B for Isolated Loop Circuit Protection
- Response Time is Typically < 1 ns
- SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- Pb-Free Packages are Available**

Mechanical Characteristics:

CASE: Void-free, transfer-molded, thermosetting plastic **FINISH:** All external surfaces are corrosion resistant and leads are readily solderable

MAXIMUM CASE TEMPERATURE FOR SOLDERING PURPOSES: 260°C for 10 Seconds

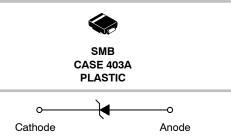
LEADS: Modified L–Bend providing more contact area to bond pads **POLARITY:** Cathode indicated by polarity band **MOUNTING POSITION:** Any



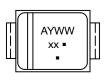
ON Semiconductor®

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PLASTIC SURFACE MOUNT ZENER OVERVOLTAGE TRANSIENT SUPPRESSORS 5.8–171 VOLTS 600 WATT PEAK POWER



MARKING DIAGRAM



A = Assembly Location

- Y = Year
- WW = Work Week
- xx = Device Code (Refer to page 3)

= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
P6SMBxxxAT3G	SMB (Pb-Free)	2,500 / Tape & Reel
SZP6SMBxxxAT3G	SMB (Pb-Free)	2,500 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*Please see P6SMB11CAT3 to P6SMB91CAT3 for Bidirectional devices.

**For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Power Dissipation (Note 1) @ $T_L = 25^{\circ}C$, Pulse Width = 1 ms	P _{PK}	600	W
DC Power Dissipation @ T _L = 75°C Measured Zero Lead Length (Note 2) Derate Above 75°C Thermal Resistance from Junction-to-Lead	P _D R _{θJL}	3.0 40 25	W mW/°C °C/W
DC Power Dissipation (Note 3) @ T _A = 25°C Derate Above 25°C Thermal Resistance from Junction-to-Ambient	P _D R _{θJA}	0.55 4.4 226	W mW/°C °C/W
Forward Surge Current (Note 4) @ $T_A = 25^{\circ}C$	I _{FSM}	100	А
Operating and Storage Temperature Range	T _J , T _{stg}	-65 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. 10 X 1000 µs, non-repetitive

1" square copper pad, FR-4 board
 FR-4 board, using ON Semiconductor minimum recommended footprint, as shown in 403A case outline dimensions spec.

4. 1/2 sine wave (or equivalent square wave), PW = 8.3 ms, duty cycle = 4 pulses per minute maximum.

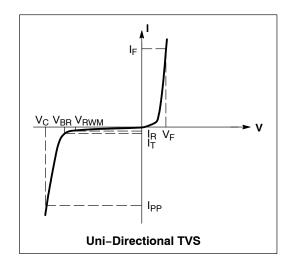
ELECTRICAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise noted}, V_F = 3.5 \text{ V Max.} @$

I_F (Note 4) = 30 A) (Note 5)

,						
Symbol	Parameter					
I _{PP}	Maximum Reverse Peak Pulse Current					
V _C	Clamping Voltage @ I _{PP}					
V _{RWM}	Working Peak Reverse Voltage					
I _R	Maximum Reverse Leakage Current @ V _{RWM}					
V_{BR}	Breakdown Voltage @ I _T					
Ι _Τ	Test Current					
ΘV_{BR}	Maximum Temperature Coefficient of V_{BR}					
١ _F	Forward Current					
V _F	Forward Voltage @ I _F					

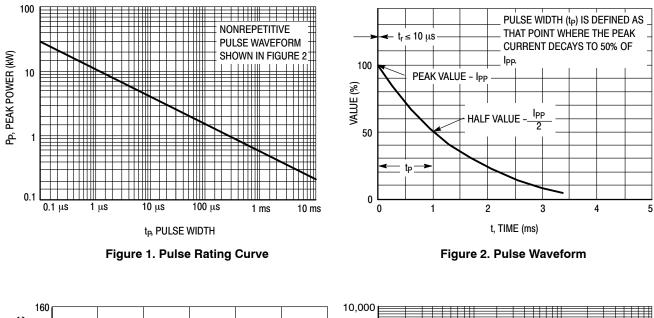
5. 1/2 sine wave or equivalent, PW = 8.3 ms, non-repetitive duty cycle

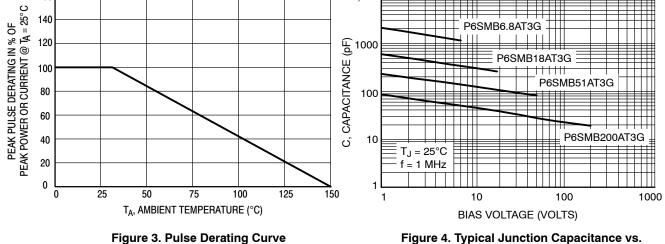


ELECTRICAL CHARACTERISTICS

		V _{RWM}	I _B @	Breakdown Voltage				V _C @ I _{PP} (Note 8)			C _{typ}
	Device	(Note 6)	V _{RWM}	V _{BR} V (Note 7) @ I _T			V _C I _{PP}		ΘV _{BR}	(Note 9)	
Device*	Marking	v	μ Α	Min	Nom	Max	mA	v	Α	%/°C	pF
P6SMB6.8AT3G P6SMB7.5AT3G P6SMB8.2AT3G P6SMB9.1AT3G	6V8A 7V5A 8V2A 9V1A	5.8 6.4 7.02 7.78	1000 500 200 50	6.45 7.13 7.79 8.65	6.8 7.51 8.2 9.1	7.14 7.88 8.61 9.55	10 10 10 1	10.5 11.3 12.1 13.4	57 53 50 45	0.057 0.061 0.065 0.068	2380 2180 2015 1835
P6SMB10AT3G P6SMB12AT3G P6SMB13AT3G	10A 12A 13A	8.55 10.2 11.1	10 5 5	9.5 11.4 12.4	10 12 13.05	10.5 12.6 13.7	1 1 1	14.5 16.7 18.2	41 36 33	0.073 0.078 0.081	1690 1435 1335
P6SMB15AT3G P6SMB16AT3G P6SMB18AT3G P6SMB20AT3G	15A 16A 18A 20A	12.8 13.6 15.3 17.1	5 5 5 5	14.3 15.2 17.1 19	15.05 16 18 20	15.8 16.8 18.9 21	1 1 1	21.2 22.5 25.2 27.7	28 27 24 22	0.084 0.086 0.088 0.09	1175 1110 1000 910
P6SMB22AT3G P6SMB24AT3G P6SMB27AT3G P6SMB30AT3G	22A 24A 27A 30A	18.8 20.5 23.1 25.6	5 5 5 5	20.9 22.8 25.7 28.5	22 24 27.05 30	23.1 25.2 28.4 31.5	1 1 1	30.6 33.2 37.5 41.4	20 18 16 14.4	0.092 0.094 0.096 0.097	835 775 700 635
P6SMB33AT3G P6SMB36AT3G P6SMB39AT3G P6SMB43AT3G	33A 36A 39A 43A	28.2 30.8 33.3 36.8	5 5 5 5	31.4 34.2 37.1 40.9	33. <i>05</i> 36 39.05 43.05	34.7 37.8 41 45.2	1 1 1	45.7 49.9 53.9 59.3	13.2 12 11.2 10.1	0.098 0.099 0.1 0.101	585 540 500 460
P6SMB47AT3G P6SMB51AT3G P6SMB56AT3G P6SMB62AT3G	47A 51A 56A 62A	40.2 43.6 47.8 53	5 5 5 5	44.7 48.5 53.2 58.9	47.05 51.05 56 62	49.4 53.6 58.8 65.1	1 1 1 1	64.8 70.1 77 85	9.3 8.6 7.8 7.1	0.101 0.102 0.103 0.104	425 395 365 335
P6SMB68AT3G P6SMB75AT3G P6SMB82AT3G P6SMB91AT3G	68A 75A 82A 91A	58.1 64.1 70.1 77.8	5 5 5 5	64.6 71.3 77.9 86.5	68 75.05 82 91	71.4 78.8 86.1 95.5	1 1 1	92 103 113 125	6.5 5.8 5.3 4.8	0.104 0.105 0.105 0.106	305 280 260 235
P6SMB100AT3G P6SMB110AT3G P6SMB120AT3G P6SMB130AT3G	100A 110A 120A 130A	85.5 94 102 111	5 5 5 5	95 105 114 124	100 110.5 120 130.5	105 116 126 137	1 1 1 1	137 152 165 179	4.4 4.0 3.6 3.3	0.106 0.107 0.107 0.107	215 200 185 170
P6SMB150AT3G P6SMB160AT3G P6SMB180AT3G	150A 160A 180A	128 136 154	5 5 5	143 152 171	150.5 160 180	158 168 189	1 1 1	207 219 246	2.9 2.7 2.4	0.108 0.108 0.108	150 140 130
P6SMB200AT3G	200A	171	5	190	200	210	1	274	2.2	0.108	115

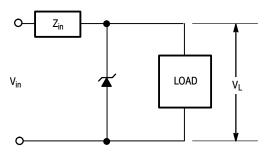
6. A transient suppressor is normally selected according to the working peak reverse voltage (V_{RWM}), which should be equal to or greater than the DC or continuous peak operating voltage level.
7. V_{BR} measured at pulse test current I_T at an ambient temperature of 25°C.
8. Surge current waveform per Figure 2 and derate per Figure 3.
9. Bias Voltage = 0 V, F = 1 MHz, T_J = 25°C
* Include SZ-prefix devices where applicable.





Bias Voltage





APPLICATION NOTES

Response Time

In most applications, the transient suppressor device is placed in parallel with the equipment or component to be protected. In this situation, there is a time delay associated with the capacitance of the device and an overshoot condition associated with the inductance of the device and the inductance of the connection method. The capacitive effect is of minor importance in the parallel protection scheme because it only produces a time delay in the transition from the operating voltage to the clamp voltage as shown in Figure 5.

The inductive effects in the device are due to actual turn-on time (time required for the device to go from zero current to full current) and lead inductance. This inductive effect produces an overshoot in the voltage across the equipment or component being protected as shown in Figure 6. Minimizing this overshoot is very important in the application, since the main purpose for adding a transient suppressor is to clamp voltage spikes. The SMB series have a very good response time, typically < 1 ns and negligible inductance. However, external inductive effects could produce unacceptable overshoot. Proper circuit layout,

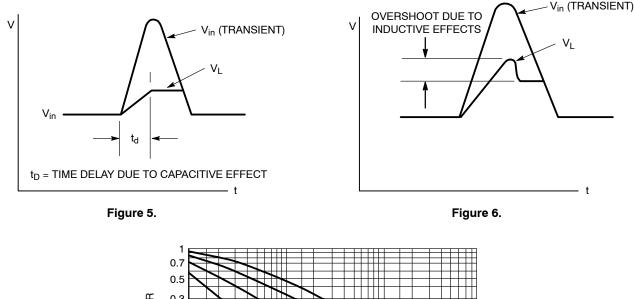
minimum lead lengths and placing the suppressor device as close as possible to the equipment or components to be protected will minimize this overshoot.

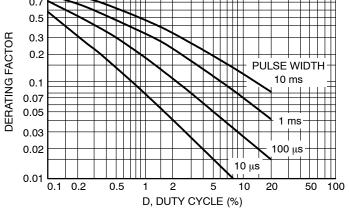
Some input impedance represented by Z_{in} is essential to prevent overstress of the protection device. This impedance should be as high as possible, without restricting the circuit operation.

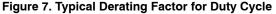
Duty Cycle Derating

The data of Figure 1 applies for non-repetitive conditions and at a lead temperature of 25°C. If the duty cycle increases, the peak power must be reduced as indicated by the curves of Figure 7. Average power must be derated as the lead or ambient temperature rises above 25°C. The average power derating curve normally given on data sheets may be normalized and used for this purpose.

At first glance the derating curves of Figure 7 appear to be in error as the 10 ms pulse has a higher derating factor than the 10 μ s pulse. However, when the derating factor for a given pulse of Figure 7 is multiplied by the peak power value of Figure 1 for the same pulse, the results follow the expected trend.







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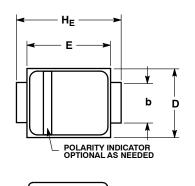
UL RECOGNITION

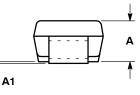
The entire series has *Underwriters Laboratory Recognition* for the classification of protectors (QVGQ2) under the UL standard for safety 497B and File #E210057. Many competitors only have one or two devices recognized or have recognition in a non-protective category. Some competitors have no recognition at all. With the UL497B recognition, our parts successfully passed several tests including Strike Voltage Breakdown test, Endurance Conditioning, Temperature test, Dielectric Voltage-Withstand test, Discharge test and several more.

Whereas, some competitors have only passed a flammability test for the package material, we have been recognized for much more to be included in their Protector category.

PACKAGE DIMENSIONS

SMB CASE 403A-03 **ISSUE H**

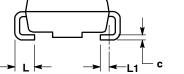


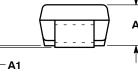


NOTES 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2 CONTROLLING DIMENSION: INCH

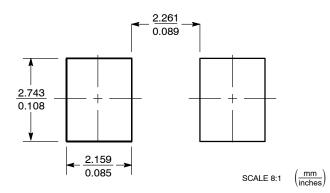
3. D DIMENSION SHALL BE MEASURED WITHIN DIMENSION P.

	м	ILLIMETE	RS	INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	1.90	2.20	2.28	0.075	0.087	0.090	
A1	0.05	0.10	0.19	0.002	0.004	0.007	
b	1.96	2.03	2.20	0.077	0.080	0.087	
с	0.15	0.23	0.31	0.006	0.009	0.012	
D	3.30	3.56	3.95	0.130	0.140	0.156	
E	4.06	4.32	4.60	0.160	0.170	0.181	
HE	5.21	5.44	5.60	0.205	0.214	0.220	
L	0.76	1.02	1.60	0.030	0.040	0.063	
L1	0.51 REF			0.020 REF			





SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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